## BAS16W1

## Ultra High Speed Switching Diodes

These Silicon Epitaxial Planar Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC-88 package which is designed for low power surface mount applications.

## Features

- Fast $t_{\mathrm{rr}},<3.0 \mathrm{~ns}$
- Low $\mathrm{C}_{\mathrm{D}},<2.0 \mathrm{pF}$
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right)$

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 100 | V |
| Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 100 | V |
| Forward Current (Note 1) | $\mathrm{I}_{\mathrm{F}}$ | 200 | mAdc |
| Peak Forward Current (Note 1) | $\mathrm{I}_{\mathrm{FM}}$ | 300 | mAdc |
| Peak Forward Surge Current (10 ms) <br> (Note 1) | $\mathrm{I}_{\mathrm{FSM}}$ | 1.0 | Adc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. This is maximum rating for a single diode. In the case of using 2 or 3 diodes, the maximum ratings per diodes is $75 \%$ of the single diode.

THERMAL CHARACTERISTICS

| Rating | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Power Dissipation | $\mathrm{P}_{\mathrm{D}}$ | 300 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | $\mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor ${ }^{\circledR}$ www.onsemi.com


## MARKING DIAGRAM



RV = Specific Device Code
M = Date Code

- = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| BAS16W1T1G | SC-88 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |
| NSVBAS16W1T1G | SC-88 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## BAS16W1

ELECTRICAL CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right)$

| Characteristic | Symbol | Condition | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Reverse Voltage Leakage Current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=30 \mathrm{~V}$ | - | 0.1 | $\mu \mathrm{Adc}$ |
|  |  | $\mathrm{V}_{\mathrm{R}}=80 \mathrm{~V}$ | - | 0.5 |  |
|  |  | $\mathrm{V}_{\mathrm{R}}=100 \mathrm{~V}$ | - | 1.0 |  |
| Forward Voltage | $V_{F}$ | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$ | - | 0.72 | Vdc |
|  |  | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | - | 0.85 |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=50 \mathrm{~mA}$ | - | 1.0 |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | - | 1.2 |  |
| Reverse Breakdown Voltage | $\mathrm{V}_{\mathrm{R}}$ | $\mathrm{I}_{\mathrm{R}}=100 \mu \mathrm{~A}$ | 100 | - | Vdc |
| Diode Capacitance | $\mathrm{C}_{\mathrm{D}}$ | $\mathrm{V}_{\mathrm{R}}=0, \mathrm{f}=1.0 \mathrm{MHz}$ | - | 2.0 | pF |
| Reverse Recovery Time (Figure 1) | $\mathrm{t}_{\mathrm{rr}}$ (Note 2) | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6.0 \mathrm{~V}, \\ & \mathrm{R}_{\mathrm{L}}=100 \Omega, \mathrm{I}_{\mathrm{rr}}=0.1 \mathrm{I}_{\mathrm{R}} \end{aligned}$ | - | 3.0 | ns |

2. $\mathrm{t}_{\mathrm{rr}}$ Test Circuit

RECOVERY TIME EQUIVALENT TEST CIRCUIT


INPUT PULSE


OUTPUT PULS

$\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$
$\mathrm{V}_{\mathrm{R}}=6 \mathrm{~V}$
$\mathrm{R}_{\mathrm{L}}=100 \Omega$

Figure 1. Reverse Recovery Time Equivalent Test Circuit


Figure 2. Forward Voltage


Figure 3. Leakage Current


Figure 4. Capacitance


RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 2. CONTROLLING DIMENSION: MILLIMETERS.
2. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
3. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DIMENSIONS D AND E1 AT THE OUT
THE PLASTIC BODY AND DATUM H.
THE PLAST AND B ARE DETERMINED AT DATUM H.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND c APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
6. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | -- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |
|  | GENERIC |  |  |  |  |  |
|  | MARKING DIAGRAM* |  |  |  |  |  |



XXX = Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-F r e e$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


## STYLES ON PAGE 2

| DOCUMENT NUMBER: | 98ASB42985B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontroled except when stamped "CONTROLLED COPY" in red. |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-88/SC70-6/SOT-363 | PAGE 1 OF 2 |

[^0] rights of others.

## SC-88/SC70-6/SOT-363

CASE 419B-02
ISSUE Y
STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 19:
PIN 1. IOUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF
STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1
STYLE 2:

CANCELLED
STYLE 8:
CANCELLED

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR
STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAAN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

| STYLE 3 : CANCELLED | STYLE 4: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. ANODE | STYLE 5: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. CATHODE | STYLE 6 : <br> PIN 1. ANODE 2 <br> 2. $\mathrm{N} / \mathrm{C}$ <br> 3. CATHODE 1 <br> 4. ANODE 1 <br> 5. N/C <br> 6. CATHODE 2 |
| :---: | :---: | :---: | :---: |
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: |
| PIN 1. EMITTER 2 | PIN 1. SOURCE 2 | PIN 1. CATHODE 2 | PIN 1. ANODE 2 |
| 2. EMITTER 1 | 2. SOURCE 1 | 2. CATHODE 2 | 2. ANODE 2 |
| 3. COLLECTOR 1 | 3. GATE 1 | 3. ANODE 1 | 3. CATHODE 1 |
| 4. BASE 1 | 4. DRAIN 1 | 4. CATHODE 1 | 4. ANODE 1 |
| 5. BASE 2 | 5. DRAIN 2 | 5. CATHODE 1 | 5. ANODE 1 |
| 6. COLLECTOR 2 | 6. GATE 2 | 6. ANODE 2 | 6. CATHODE 2 |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. $\mathrm{N} / \mathrm{C}$ | 2. GND | 2. CH 1 | 2. ANODE |
| 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. N/C | 5. VBUS | 5. CH 2 | 5. CATHODE |
| 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 27: | STYLE 28: | STYLE 29: | STYLE 30: |
| PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

| DOCUMENT NUMBER: | 98ASB42985B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-88/SC70-6/SOT-363 | PAGE 2 OF 2 |

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.
onsemi, OnSeMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com
onsemi Website: www.onsemi.com

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Diodes - General Purpose, Power, Switching category:
Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :
RD0306T-H BAQ33-GS18 BAV17-TR BAV19-TR 1N3611 NTE156A NTE525 NTE571 NTE574 NTE5804 NTE5806 NTE6244 1SS181-TP 1SS193,LF 1SS400CST2RA SDAA13 SHN2D02FUTW1T1G LS4151GS08 1N4449 1N456A 1N4934-E3/73 1N914B 1N914BTR RFUH20TB3S BAS 28 E6327 BAV199-TP BAW56DWQ-7-F BAW56M3T5G BAW75-TAP MM230L-CAA IDW40E65D1 JAN1N3600 LL4151-GS18 053684A SMMSD4148T3G 707803H NSVDAN222T1G SP000010217 ACDSW4448-HF CDSZC01100-HF BAV199E6433HTMA1 BAV70M3T5G SMBT2001T1G NTE5801 NTE5800 NTE5808 NTE6240 NTE6248 DLM10C-AT1 BAS28-7


[^0]:    ON Semiconductor and (ON) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the

